

Rev. V6

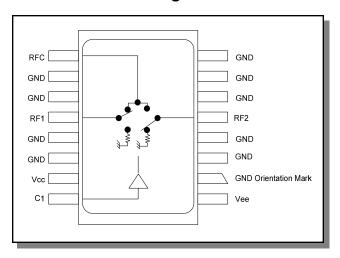
#### **Features**

- Integral TTL Driver
- Low DC Power Consumption
- · Fast Switching Speed: 7 ns Typical
- Hermetic Surface Mount Package
- 50 Ohm Nominal Impedance
- MIL-STD-883 Screening Available
- Lead-Free CR-9 Package
- 260°C Reflow Compatible
- RoHS\* Compliant

### **Description**

M/A-COM's SW-313-PIN is a GaAs FET SPDT absorptive switch with integral silicon ASIC driver. Packaged in a 16-lead ceramic surface mount package, this device offers excellent performance and repeatability from DC to 3 GHz while maintaining low power consumption. The SW-313-PIN is ideally suited for use where fast speed, low power consumption and broadband applications are required. MIL-STD-883 screening available.

### **Functional Block Diagram**



## **Ordering Information**

Part Number	Package		
SW-313-PIN	Bulk Packaging		
SW-313-TB	Sample Test Board		

Note: Reference Application Note M513 for reel size information.

## **Pin Configuration**

Pin No.	Function	Pin No.	Function
1	Vee	9	RFC
2	GND	10	GND
3	GND	11	GND
4	GND	12	RF1
5	RF2	13	GND
6	GND	14	GND
7	GND	15	Vcc
8	GND	16	C1

The metal bottom of the case must be connected to RF and DC ground.

<sup>\*</sup> Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.

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# Electrical Specifications: (From –55°C to +85°C), $Z_0 = 50\Omega^{1,2}$

Parameter	Test Conditions	Frequency	Units	Min	Тур	Max
Insertion Loss	_	DC - 3000 MHz DC - 2000 MHz DC - 1000 MHz DC - 500 MHz	dB dB dB dB	_ _ _ _	_ _ _	1.2 1.1 0.9 0.8
VSWR	_	DC - 3000 MHz DC - 2000 MHz DC - 1000 MHz DC - 500 MHz	Ratio Ratio Ratio Ratio	_ _ _	_ _ _	1.50:1 1.40:1 1.35:1 1.30:1
Isolation	_	DC - 3000 MHz DC - 2000 MHz DC - 1000 MHz DC - 500 MHz	dB dB dB dB	35 43 48 53	_ _ _	
Trise, Tfall	10% to 90%	_	ns	_	7	_
Ton, Toff	1.3V CTL to 90% / 10%	_	ns	_	18	_
Transients	In-Band	_	mV	_	25	_
1 dB Compression	Input Power	0.05 GHz 0.5 GHz to 3 GHz	dBm dBm	_	+25 +30	_
IP2	Two-Tone Input Power up to +5 dBm	0.05 GHz 0.5 GHz to 3 GHz	dBm dBm	_	+60 +65	_
IP3	Two-Tone Input Power up to +5 dBm	0.05 GHz 0.5 GHz to 3 GHz	dBm dBm	_	+40 +46	_
Vin Low	0V to 0.8V	_	μΑ	_	_	1
Vin High	2.0V to 5.0V	_	μΑ	_	_	1
Vcc	+5.0V ± 10%	_	mA	_	_	1
Vee	-5.0V to -8.0V	_	mA	_	_	1

<sup>1.</sup> All specifications apply when operated with bias voltages of +5V for Vcc and -5V for Vee.

<sup>2.</sup> When DC blocks are used, a 10K ohm return to GND is required on the RFC port.

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## Absolute Maximum Ratings 3,4

Parameter	Absolute Maximum	
Max Input Power 50 MHz 500 - 3000 MHz	+27 dBm +34 dBm	
V <sub>CC</sub>	-0.5V ≤ V <sub>CC</sub> ≤ +7.0V	
V <sub>EE</sub>	-8.5V ≤ V <sub>EE</sub> ≤ +0.5V	
V <sub>CC</sub> - V <sub>EE</sub>	$-0.5V \le V_{CC} - V_{EE} \le 14.5V$	
Vin <sup>5</sup>	-0.5V ≤ Vin ≤ V <sub>CC</sub> + 0.5V	
Operating Temperature	-55°C to +125°C	
Storage Temperature	-65°C to +150°C	

- 3. Exceeding any one or combination of these limits may cause permanent damage to this device.
- M/A-COM does not recommend sustained operation near these survivability limits.
- Standard CMOS TTL interface, latch-up will occur if logic signal is applied prior to power supply.

### **Handling Procedures**

Please observe the following precautions to avoid damage:

# Static Sensitivity

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

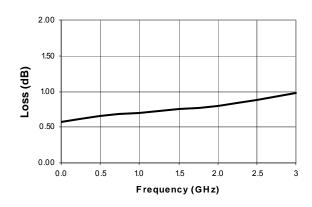
#### **Truth Table (Switch)**

0	Condition of Switch		
Control Input	RF Common to Each RF Port		
C1	RF1	RF2	
0	On	Off	
1	Off	On	

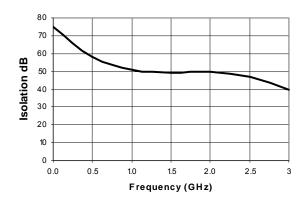
0 = TTL Low; 1 = TTL High

### **Typical Performance Curves**

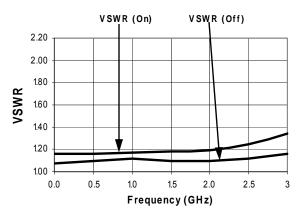
#### Insertion Loss vs. Frequency



#### Isolation vs. Frequency



#### VSWR vs. Frequency

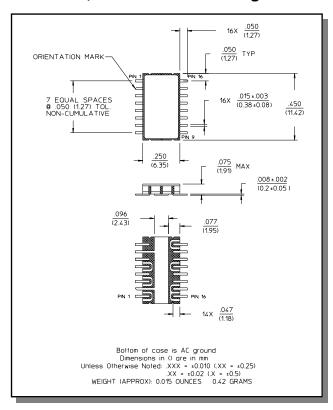


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# Lead-Free, CR-9 Ceramic Package<sup>†</sup>



<sup>&</sup>lt;sup>†</sup> Reference Application Note M538 for lead-free solder reflow recommendations.

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